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Electronic and magnetic properties of the $BaTiO_3/LaMnO_3$ interface: a DFT study

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Abstract By means of *ab initio* calculations withing the density functional theory (DFT) electronic and magnetic properties of $BaTiO_3/LaMnO_3$ interface were investigated. An impact of ferroelectric overlayer thickness onto the interface properties was analysed through the spin-polarized density of states.

Keywords ferroelectric interface · magnetoelectric coupling · DFT

1 Introduction

The $LaAlO_3/SrTiO_3$ (LAO/STO) heterostructure has been widely investigated during last 20 years after the two-dimensional gas (2DEG) observation at the interface of that system [1]. It was also found the conducting state coexists with magnetic state. The arising magnetic order in the LAO/STO system is a matter of intensive discussion [2,3]. From *ab initio* calculations it was revealed that the bare heterostructure is nonmagnetic, and magnetic ordering was related to defects formation, in particular, to oxygen vacancies at the interface and/or the surface [2,4]. The arising magnetization is weak and in according to Ref. [4] the maximal magnetic moment per Ti atom equals to 0.232 μ_B.

Besides, below 300 mK LAO/STO system passes into the superconducting state [5]. Recently, in one of our previous research by means of *ab initio* it was demonstrated that the usage of the high-temperature superconductor (PCHTSC), La_2CuO_4 (LCO), as a substrate and ferroelectric oxide $BaTiO_3$ in the heterostructure as an overlayer may result in conducting state located mostly at the interfacial LCO layer. Lately, a high-temperature quasi-two-dimensional superconducting state has been observed in the $Ba_{0.8}Sr_{0.2}TiO_3/La_2CuO_4$ heterostructure with T_c=30 K [6]. This T_c is 100 times larger than Tc in LAO/STO [5].

The experimental observation of conducting state was also realized in the $Ba_{0.8}Sr_{0.2}TiO_3$/ $LaMnO_3$ system [7]. Such a heterostructute is composed of a ferromagnet which can serve as a source of magnetic state and a antiferroelectric which can be used as a tool for electron doping [8,9]. Hence, in the $LaMnO_3/BaTiO_3$ (LMO/BTO) heterointerface it is expected to have the interfacial magnetism along with conducting state. It presented paper we investigate the possibilities of the spin-polarized 2DEG appearing in the LMO/BTO heterostructure. The essential issue is to understand the impact of the ferroelectric BTO slab thickness on the interface electronic and magnetic states. In order to do so we investigate the BTO/LMO heterostructure with varying number of BTO overlayers and analyse the density of state spectrum.

2 Calculation details

The *ab initio* calculations were based on density functional theory (DFT) [10,11]. Exchange and correlation effects were accounted for by the generalized gradient approximation (GGA) as parametrized by Perdew, Burke, and Ernzerhof (PBE) [12]. The Kohn-Sham equations were solved with projector-augmented-wave (PAW) potentials and wave functions [13] as implemented in the Vienna Ab-Initio Simulation Package (VASP) [14,15, 16], which is part of the MedeA® software of Materials

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Design [17]. Specifically, we used a plane-wave cutoff of 400 eV. The force tolerance was 0.05 eV/Å and the energy tolerance for the self-consistency loop was 10^{-5} eV. The Brillouin zones were sampled using Monkhorst-Pack grids [18] including $5 \times 5 \times 1$ **k**-points. A set of calculations was carried out with a $+U$ correction applied to Mn $3d$, Ti $3d$ and La $4f$ states [19]. A simplified Dudarev approach was used [20]: the U values of 4 eV for Mn, 2 eV for Ti and 8 eV for La states were applied.

The heterostructures were modelled by a central region of $LaMnO_3$ comprising $2\frac{1}{2}$ unit cells with LaO termination on both sides and varying number of $BaTiO_3$ overlayers with TiO_2 termination towards the central slab and BaO surface termination also on both sides. In order to avoid interaction of the surfaces and slabs with their periodic images, ≈20 Å-wide vacuum region was added.

3 Bulk components

First, the parent materials of the heterointerface have been checked separately in the bulk geometry in order to ensure the reproducibility of the results obtained by the method and computational parameters used in the present research.

Starting from the experimental structure of bulk $LaMnO_3$, the lattice constants and atomic positions were fully relaxed. To realize the spin-dependent switching effect, which was mentioned in the introduction, it was suggested to replace FM material by AFM [8]. The spin-polarized density of states (DOS) plot for the A-AFM LMO in the bulk configuration in presented in Fig. 1. The bulk LMO is a semiconductor, with an O $2p$ dominated valence band, with Mn $3d$ contribution. The calculated band gap and magnetic moment of the Mn atom equal 1.349 eV and 3.832 μ_B, respectively. Those values agree well with experimental ones of 1.7 eV and $3.7 \pm 0.1\ \mu_B$, respectively [21]. Based on this comparison we concluded that the chosen value of the U parameter can yield relatively correctly both the energy gap and the magnetization. Besides, the calculated cell parameters, shown in Table 1, were found to be close to experimental values [22] and also to the previous *ab initio* research, for example Ref. [23].

$BaTiO_3$ is one of the most well known ferroelectric, which has a ferroelectric polarization in a tetragonal system with moderate polarization of 26 $\mu C/cm^2$ [25]. Calculated energies per unit cells, band gaps, oxygen displacements and polarization for the cubic, tetragonal and orthorhombic phases are presented in Table 2. All calculated values agree well with experimental data. The experimental band gap is higher than the computed one, but the difference is reasonable for the DFT.

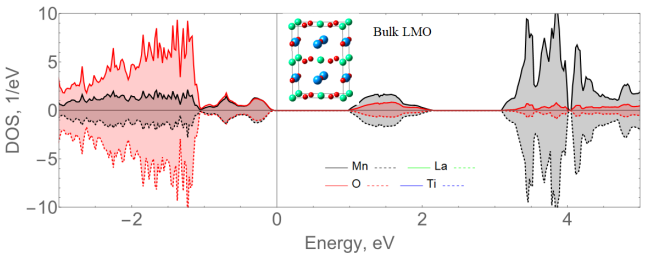


Fig. 1 Density of states spectra for the A-AFM bulk $LaMnO_3$ along with the corresponding unit cell structure.

Table 1 Calculated lattice constants in Å of bulk $LaMnO_3$, bulk $BaTiO_3$ and a rotated by 45° along z-axis $BaTiO_3$ unit cell in order to merge with the $LaMnO_3$ unit cell. The last row lists the $BaTiO_3/LaMnO_3$ supercell lattice constants. Experimental data are presented as well for comparison.

	a	b	c
LMO	5.709	5.675	8.018
Expt. [22]	5.742	5.532	7.669
BTO	3.986	3.986	4.014
Expt. [24]	3.992	3.992	4.036
BTO ($\times\sqrt{2}$)	5.637	5.637	4.014
Supercell	5.709	5.675	50

Table 2 Calculated energy (E) per unit cell, c/a ratio, the band gaps (ε), displacement of Ti atoms with respect to the O planes ($\triangle$) and polarization **P** in $\mu C/cm^2$ of the cubic, tetragonal and orthorombic phases of bulk $BaTiO_3$. Experimental values are given for the tetragonal phase.

Phase	c/a	ε, eV	$\triangle$, Å	**P**
Cubic	1	2.169	0	0
Tetragonal	1.007	2.249	0.13	31
Expt.	1.010 [26]	3.27 [27]	0.15 [26]	26 [25]
Orthorhombic	1.428	2.259	0.09	

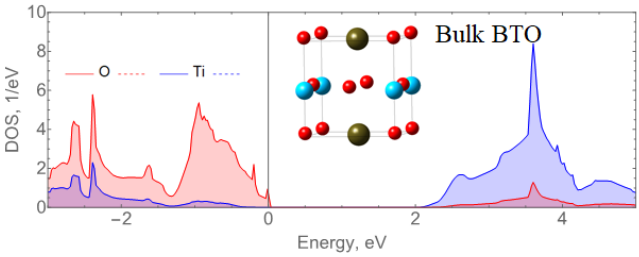


Fig. 2 Density of states spectra for the bulk $BaTiO_3$ along with the corresponding unit cell structure.

For the purpose of the present work we are interested in the phases with spontaneous polarization, hence, we will focus on the tetragonal BTO structure. The calculated lattice parameters along with experimental ones are listed in Table 1. The calculated density of state spectra for the bulk BTO is given in Fig. 2.

3.1 $LaMnO_3/BaTiO_3$ heterostructure

In order to merge BTO with LMO so that the polarization is parallel to the easy axis of antiferromagnet, the BTO unit cell has to be rotated by 45° along z-axis. As listed in Table 1 $a_{BTO} \times \sqrt{2}$ are very close to the a_{LMO} and b_{LMO} cell parameters. The resulted supercell with two BTO overlayers is presented in Fig. 3 a, where the right half of the unit cell is presented without full vacuum region. The structure was fully optimized.

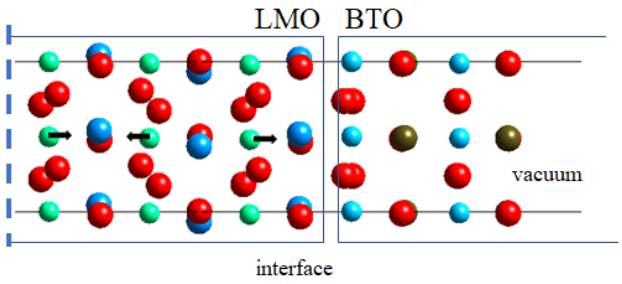


Fig. 3 The fully optimized half-right structure of LMO/2BTO heterointerface. The supercell is displayed without the vacuum region, which was 20Å. Arrows indicate magnetic moments directions in the LMO slab. b) Corresponding atom-resolved density of states for the heterostructure with two BTO overlayer and c) with three BTO overlayers.

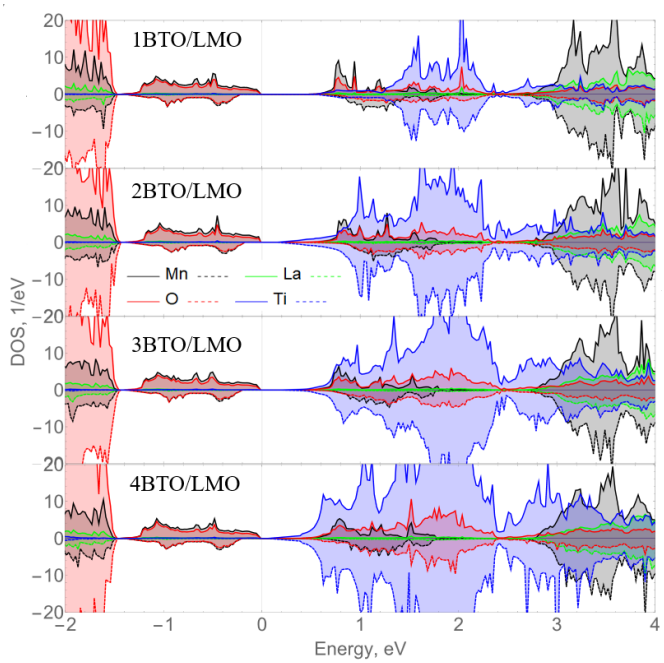


Fig. 4 Atom-resolved density of states spectra for the heterostructure with varying number (1-4) BTO overlayers.

Performed structural optimization resulted in the insignificant shift of Ti atoms out of oxygen planes (Δz_{Ti-O}). For the heterostructure with two BTO overlayers Δz_{Ti-O} distances within the interfacial layer equal to -0.046 Å and 0.247 Å, within the surface layer shifts are less significant and equal to 0.049 Å and 0.101 Å, respectively. Except for the one, all the movements of Ti are towards the surface, which leads to the total polarization predominantly towards the surface. Such a structural reconstruction leads to the electronic rearrangement as reflected in the DOS spectra shown in Fig. 4 a – d for varying number of BTO layers. With increasing the number of BTO overlayers the band gap decreases from 0.47 eV for heterostructure with one BTO overlayer to 0.113 eV with four. Such a decay of the band gap with the number of overlayers differs from LAO/STO linear dependence as shown in Fig. 5. Indeed, the band gap decrease with increase of LAO overlayers in LAO/STO associated with increase of the field directed towards the surface. As soon as this field overcomes the field arising due do the structural relaxation, the LAO/STO system becomes conductor. That happens above 4 LAO overlayers in according to our previous *ab initio* research [4]. In contract, in the LMO/BTO heterostructure without polar overlayers the field towards the surface originates from the ferroelectric polarization. Since the slope in Fig. 5 for LMO/BTO in smaller it is obvious that the ferroelectric field is weaker and conductivity occurs with more overlayers. Note, that in experiments [7] the thickness of the ferroelectric film was about 350 nm, and based on the asymptotics of our calculations it is expected that the band gap vanishes completely at such a thickness.

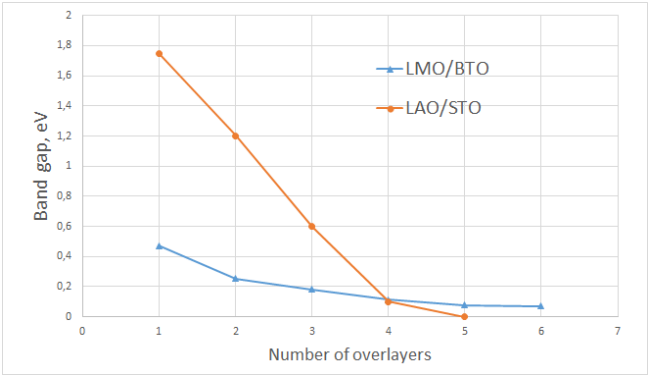


Fig. 5 Calculated band gap versus the number of BTO overlayers in LMO/BTO heterostructure along with analogous dependence for LAO/STO systems for comparison.

Finally, the LMO/BTO system possesses relatively high total magnetization due to the odd number of MnO layers with magnetic moment per Mn equal to 3.8 μ_B. Ferromagnetic magnetization should increase with increasing the electron doping.

4 Conclusions

In the present paper by means of DFT+U calculation the electronic and magnetic properties of bulk $LaMnO_3$ and $BaTiO_3$, as well as LMO/BTO heterostructure have been demonstrated. Within the chosen approach and computational parameters the bulk components of the heterostructure were confirmed to be insulators. In the heterostructure geometry the decrease of the band gap with increasing the number of BTO overlayers was demonstrated. It was found that the curve tends to zero, but the system remains semiconductor up to six BTO overlayers. It means that the conducting state arises with more ferroelectric overlayers, that is consistent with experiment from Ref. [7] where the thickness of ferroelectric film was much higher. It was shown that the LMO/BTO systen possesses relatively high total magnetization, which is expected to increase with increasing the electron doping.

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Conflict of interest

The authors declare that they have no conflict of interest.

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